

Title (en)

METAL OXIDE FIELD EFFECT TRANSISTORS ON A MECHANICALLY FLEXIBLE POLYMER SUBSTRATE HAVING A DIELECTRIC THAT CAN BE PROCESSED FROM SOLUTION AT LOW TEMPERATURES

Title (de)

METALLOXID-FELDEFFEKTTRANSISTOREN AUF MECHANISCH FLEXIBLEM POLYMERSUBSTRAT MIT AUS LÖSUNG PROZESSIERBAREM DIELEKTRIKUM BEI NIEDRIGEN TEMPERATUREN

Title (fr)

TRANSISTORS À EFFET DE CHAMP À GRILLE MÉTAL-OXYDE SUR SUBSTRAT POLYMÈRE FLEXIBLE MÉCANIQUE COMPORTANT UN DIÉLECTRIQUE POUVANT ÊTRE TRAITÉ À PARTIR D'UNE SOLUTION À BASSES TEMPÉRATURES

Publication

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Application

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Abstract (en)

[origin: WO2011073044A1] The present invention relates to a method for producing an electronic component, in particular a field-effect transistor (FET), comprising at least one substrate, at least one dielectric, and at least one semiconducting metal oxide, wherein the dielectric or a precursor compound thereof based on organically modified silicon oxide compounds, in particular based on silsequioxanes and/or siloxanes, can be processed out of solution, and is thermally treated at a low temperature from room temperature to 350 °C, and the semiconductive metal oxide, in particular ZnO or a precursor compound thereof, can also be processed from solution at a low temperature from room temperature to 350 °C.

IPC 8 full level

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